

# SANYO Semiconductors DATA SHEET

NPN Epitaxial Planar Silicon Transistor

# **2SC551A** — High-Frequency Medium-Output **Amplifier Applications**

#### **Features**

- High fT : (fT=3.5GHz typ). · Large current : (IC=300mA).
- Large allowable collector dissipation (1.3W max).

## **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		40	V
Collector-to-Emitter Voltage	VCEO		30	V
Emitter-to-Base Voltage	VEBO		2	V
Collector Current	IC		300	mA
Collector Current (Pulse)	ICP		600	mA
Collector Dissipation	PC	When mounted on ceramic substrate (250mm²X0.8mm)	1.3	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
		Conditions	min	typ	max	Offic
Collector Cutoff Current	ICBO	V <sub>CB</sub> =20V, I <sub>E</sub> =0A			1.0	μΑ
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =1V, I <sub>C</sub> =0A			5.0	μΑ

Continued on next page.

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### 2SC5551A

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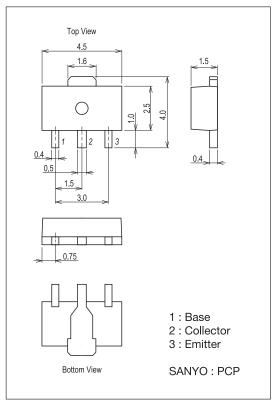
Parameter	Symbol Conditions	Conditions	Ratings			Unit
		min	typ	max	Offic	
DC Current Gain	hFE1	V <sub>CE</sub> =5V, I <sub>C</sub> =50mA	90		270	
	hFE2	VCE=5V, IC=300mA	20			
Gain-Bandwidth Product	fT	V <sub>CE</sub> =5V, I <sub>C</sub> =50mA		3.5		GHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		2.9	4.0	pF
Reverse Transfer Capacitance	Cre	V <sub>CB</sub> =10V, f=1MHz		1.5		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=50mA, IB=5mA		0.07	0.3	V
Base-to-Emitter Saturation Voltage	VBE(sat)	IC=50mA, IB=5mA		0.8	1.2	V

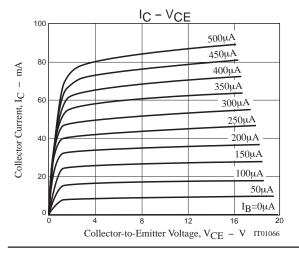
### $^{\star}$ : The 2SC5551A is classified by 50mA $h_{\mbox{\scriptsize FE}}$ as follows :

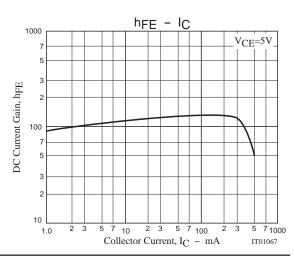
Marking	EB E	EB F
Rank	Е	F
hFE	90 to 180	135 to 270

# **Package Dimensions**

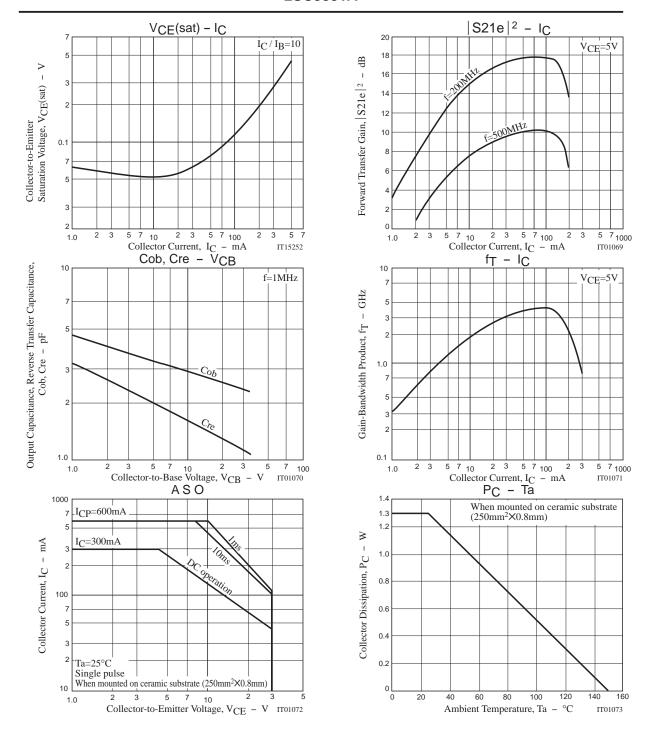
unit : mm (typ) 7007B-004







No. A1118-2/4



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